

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claim 1 (currently amended/withdrawn): 1. A method of manufacturing a filter—(10) for retaining a substance —(14)—originating from a radiation source—(12), ~~which the~~ filter ~~comprises~~ comprising a thin layer—(18) ~~which is~~ transparent to extreme ultraviolet and/or soft X-ray radiation—(16), ~~characterized in that~~ wherein the filter —(10) is resistant to high temperatures.

Claim 2 (currently amended/withdrawn): ~~A~~ The method ~~as~~ ~~claimed in~~ of claim 1, ~~characterized in that~~ wherein first the thin layer—(18) and subsequently a support structure —(20) for the thin layer—(18) are manufactured, or in reverse order, the filter—(10) being manufactured such that the thin layer—(18) is connected to the support structure—(20) in a high-temperature-resistant manner.

Claim 3 (currently amended/withdrawn): ~~A~~The method as ~~elaimed inof~~ claim 1, ~~eharacterized in that~~wherein at least the thin layer~~-(18)~~ is manufactured by means of a chemical and/or physical deposition process.

Claim 4 (currently amended/withdrawn): ~~A~~The method as ~~elaimed inof~~ claim 1, ~~eharacterized in that~~wherein at least the thin layer~~-(18)~~ comprises preponderantly zirconium, niobium, molybdenum, silicon, zirconium carbide (ZrC), zirconium dioxide, silicon carbide (SiC), silicon nitride (Si<sub>3</sub>N<sub>4</sub>), boron nitride (BN), or a combination thereof.

Claim 5 (currently amended/withdrawn): ~~A~~The method as ~~elaimed inof~~ claim 2, ~~eharacterized in that~~wherein the thin layer~~-(18)~~ and the support structure~~-(20)~~ are manufactured as an integral whole.

Claim 6 (currently amended/withdrawn): ~~A~~The method as ~~elaimed inof~~ claim 1, ~~eharacterized in that~~wherein a layer thickness~~-(22)~~ for the thin layer~~-(18)~~ of approximately 100 nm is achieved.

Claim 7 (currently amended/withdrawn): ~~A~~ The method as  
~~elaimed inof~~ claim 2, ~~characterized in that~~ wherein ~~that~~  
the support structure ~~(20)~~ comprises preponderantly  
zirconium, niobium, molybdenum, silicon, zirconium  
carbide (ZrC), zirconium dioxide, silicon carbide (SiC),  
silicon nitride (Si.sub.3N.sub.4), boron nitride (BN), or  
a combination thereof.

Claim 8 (currently amended/withdrawn): ~~A~~ The method as  
~~elaimed inof~~ claim 2, ~~characterized in that~~ wherein a  
thickness ~~(24)~~ of approximately 1 .mu.m up to 1 mm is  
adjusted for the support structure ~~(20)~~.

Claim 9 (currently amended/withdrawn): ~~A~~ The method as  
~~elaimed inof~~ claim 2, ~~characterized in that~~ wherein a  
material having a melting point of at least 1300.degree.  
C. is chosen for the thin layer ~~(18)~~ and the support  
structure ~~(20)~~.

Claim 10 (currently amended/withdrawn): ~~A~~ The method as  
~~elaimed inof~~ claim 2, ~~characterized in that~~ wherein the

support structure—(20) is constructed in the form of strips, for example forming a grid structure or honeycomb-type woven structure—(26).

Claim 11 (currently amended/withdrawn): ~~A~~ The method ~~as claimed in~~ of claim 10, ~~characterized in that~~ wherein the woven structure—(26) is generated by means of erosion, laser processing, or photochemical etching.

Claim 12 (currently amended: A device for retaining a substance—(14) originating from a radiation source—(12) ~~by means of~~ fusing a filter—(10), ~~which the~~ filter—(10) comprising ~~es~~ a thin layer—(18) that is transparent to extreme ultraviolet and/or soft X-ray radiation—(16), ~~characterized in that~~ wherein the filter—(10) is resistant to high temperatures.

Claim 13 (currently amended): ~~A~~ The device ~~as claimed in~~ of claim 12, ~~characterized in that~~ wherein the thin layer—(18) is connected to a support structure—(20) in a high-temperature-resistant manner, or in that the thin

layer-(18) and the support structure-(20) can be manufactured as an integral whole.

Claim 14 (currently amended): ~~A~~The device ~~as claimed~~  
~~in~~of claim 13, ~~characterized in that~~wherein a material  
used for the thin layer-(18) and the support structure  
-(20) has a melting point of at least 1300.degree. C.

Claim 15 (currently amended): ~~A~~The device ~~as claimed~~  
~~in~~of claim 12, ~~characterized in that~~wherein at least the  
thin layer-(18) can be manufactured by means of a  
chemical and/or physical deposition process.

Claim 16 (currently amended): ~~A~~The device ~~as claimed~~  
~~in~~of claim 12, ~~characterized in that~~wherein at least the  
thin layer-(18) comprises preponderantly zirconium,  
niobium, molybdenum, silicon, zirconium carbide (ZrC),  
zirconium dioxide, silicon carbide (SiC), silicon nitride  
(Si<sub>3</sub>N<sub>4</sub>), boron nitride (BN), or a combination thereof.

Claim 17 (currently amended): ~~The~~A device ~~as claimed~~  
~~in~~of claim 12, ~~characterized in that~~wherein the thin

layer~~-(18)~~ has a layer thickness~~-(22)~~ of approximately 100 nm.

Claim 18 (currently amended): ~~A~~The device as claimed  
~~inof~~ claim 13, ~~characterized in that~~wherein the support  
structure~~-(20)~~ has a thickness~~-(24)~~ of approximately 1  
.mu.m to 1 mm.

Claim 19 (currently amended): ~~A~~The device as claimed  
~~inof~~ claim 13, ~~characterized in that~~wherein the support  
structure~~-(20)~~ ~~can be~~is constructed in the form of  
strips, ~~for example in the form of a grid type or~~  
~~honeycomb type woven structure~~ ~~-(26)~~.

Claim 20 (currently amended): ~~A~~The device as claimed  
~~inof~~ claim 19, ~~characterized in that~~wherein the woven  
structure~~-(26)~~ ~~can be~~is obtained by means of erosion,  
laser processing, or photochemical etching.

Claim 21 (currently amended): ~~The use of the filter~~ ~~-(10)~~  
~~as claimed in claim 12 in a~~An apparatus device for EUV  
lithography comprising the device of Claim 12.

Claim 22 (currently amended): The apparatus for EUV lithography~~use as~~ claimed in claim 21, ~~characterized in that~~wherein ~~the a filter (10)~~ of the device is operated at a temperature of approximately 900.degree. C. to approximately 1300.degree. C.

Claim 23 (currently amended): The ~~use as~~apparatus for EUV lithography claimed in claim 21, ~~characterized in that~~wherein the temperature for the filter~~(10)~~ is adjustable such that the retained substance~~(14)~~ evaporates at ~~the a~~ prevailing pressure.

Claim 24 (currently amended): The ~~use as~~apparatus claimed in claim 21, ~~characterized in that~~wherein the temperature for the filter~~(10)~~ is adjustable such that the retained substance~~(14)~~ evaporates from the filter~~(10)~~ at a rate higher than that at which it is deposited thereon.

Claim 25 (currently amended): The ~~use as~~ apparatus claimed in claim 21, ~~characterized in that~~wherein a foil

trap-(28) is additionally arranged between the radiation source-(12) and the filter-(10).

Claim 26 (currently amended): The ~~use as~~ apparatus claimed in claim 21, ~~characterized in that~~ wherein the filter-(10) seals off the radiation source-(12) in the form of a window.

Claim 27 (currently amended): The ~~use as~~ apparatus claimed in claim 26, ~~characterized in that~~ wherein the substance-(14) in the radiation source-(12) reaches a partial pressure of approximately 10 Pa.

Claim 28 (new): The device of claim 19, wherein the strips are in the form of a grid-type or honeycomb-type woven structure.